

# MOSFET - Power, Single N-Channel, STD Gate, SO8-FL

40 V, 0.7 mΩ, 323 A

## NVMFWS0D7N04XM

### Features

- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Small Footprint (5 x 6 mm) with Compact Design
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Applications

- Motor Drive
- Battery Protection
- Synchronous Rectification

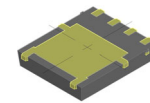
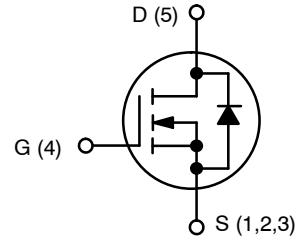
### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise stated)

| Parameter   | Symbol         | Value                     | Unit             |
|---|----------------|---------------------------|------------------|
| Drain-to-Source Voltage   | $V_{DSS}$      | 40                        | V                |
| Gate-to-Source Voltage  | $V_{GS}$       | $\pm 20$                  | V                |
| Continuous Drain Current  | $I_D$          | $T_C = 25^\circ\text{C}$  | 323              |
|   |                | $T_C = 100^\circ\text{C}$ | 229              |
| Power Dissipation   | $P_D$          | 134                       | W                |
| Continuous Drain Current  | $I_{DA}$       | $T_A = 25^\circ\text{C}$  | 9.18             |
|   |                | $T_A = 100^\circ\text{C}$ | 6.49             |
| Pulsed Drain Current  | $I_{DM}$       | 900                       | A                |
| Pulsed Source Current (Body Diode)                                | $I_{SM}$       | 900                       | A                |
| Operating Junction and Storage Temperature Range                  | $T_J, T_{STG}$ | -55 to 175                | $^\circ\text{C}$ |
| Source Current (Body Diode)                                       | $I_S$          | 202                       | A                |
| Single Pulse Avalanche Energy ( $I_{PK} = 21\text{ A}$ )          | $E_{AS}$       | 987                       | mJ               |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s) | $T_L$          | 260                       | $^\circ\text{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

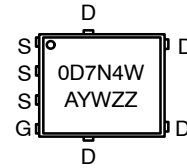
| $V_{(BR)DSS}$ | $R_{DS(on)}\text{ MAX}$ | $I_D\text{ MAX}$ |
|---------------|-------------------------|------------------|
| 40 V          | 0.7 mΩ                  | 323 A            |

### N-CHANNEL MOSFET



DFNW5 (SO-8FL)  
CASE 507BA

### MARKING DIAGRAM



- A = Assembly Location
- Y = Year
- W = Work Week
- ZZ = Lot Traceability

### ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

# NVMFWS0D7N04XM

## THERMAL CHARACTERISTICS

| Parameter  | Symbol          | Value | Unit |
|--|-----------------|-------|------|
| Thermal Resistance, Junction-to-Case (Note 2)        | $R_{\theta JC}$ | 1.11  | °C/W |
| Thermal Resistance, Junction-to-Ambient (Notes 1, 2) | $R_{\theta JA}$ | 39.3  |      |

- Surface-mounted on FR4 board using 650 mm<sup>2</sup> pad, 2 oz Cu pad.
- The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------|--------|----------------|-----|-----|-----|------|
|-----------|--------|----------------|-----|-----|-----|------|

### OFF CHARACTERISTICS

|   |                                   |   |    |      |     |       |
|---|-----------------------------------|---|----|------|-----|-------|
| Drain-to-Source Breakdown Voltage                         | $V_{(BR)DSS}$                     | $V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$   | 40 |      |     | V     |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | $\Delta V_{(BR)DSS} / \Delta T_J$ | $I_D = 250\ \mu\text{A}$ , Referenced to 25°C   |    | 14.9 |     | mV/°C |
| Zero Gate Voltage Drain Current                           | $I_{DSS}$                         | $V_{DS} = 40\text{ V}, T_J = 25^\circ\text{C}$  |    |      | 1   | μA    |
|   |                                   | $V_{DS} = 40\text{ V}, T_J = 125^\circ\text{C}$ |    |      | 40  |       |
| Gate-to-Source Leakage Current                            | $I_{GSS}$                         | $V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$     |    |      | 100 | nA    |

### ON CHARACTERISTICS

|  |                                  |   |     |      |     |       |
|--|----------------------------------|---|-----|------|-----|-------|
| Drain-to-Source On Resistance                  | $R_{DS(on)}$                     | $V_{GS} = 10\text{ V}, I_D = 50\text{ A}$ |     | 0.59 | 0.7 | mΩ    |
| Gate Threshold Voltage                         | $V_{GS(TH)}$                     | $V_{GS} = V_{DS}, I_D = 180\ \mu\text{A}$ | 2.5 | 3.0  | 3.5 | V     |
| Gate Threshold Voltage Temperature Coefficient | $\Delta V_{GS(TH)} / \Delta T_J$ | $V_{GS} = V_{DS}, I_D = 180\ \mu\text{A}$ |     | -7.2 |     | mV/°C |
| Forward Trans-conductance                      | $g_{FS}$                         | $V_{DS} = 5\text{ V}, I_D = 50\text{ A}$  |     | 244  |     | S     |

### CHARGES, CAPACITANCES & GATE RESISTANCE

|                              |              |   |                    |      |      |    |
|------------------------------|--------------|---|--------------------|------|------|----|
| Input Capacitance            | $C_{ISS}$    | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$   |                    | 4595 |      | pF |
| Output Capacitance           | $C_{OSS}$    |   |                    | 2980 |      |    |
| Reverse Transfer Capacitance | $C_{RSS}$    |   |                    | 41.8 |      |    |
| Total Gate Charge            | $Q_{G(TOT)}$ | $V_{GS} = 10\text{ V}, V_{DD} = 32\text{ V}; I_D = 50\text{ A}$ |                    | 71.6 |      | nC |
| Threshold Gate Charge        | $Q_{G(TH)}$  |   |                    | 13.5 |      |    |
| Gate-to-Source Charge        | $Q_{GS}$     |   |                    | 20.6 |      |    |
| Gate-to-Drain Charge         | $Q_{GD}$     |   |                    | 13   |      |    |
| Gate Resistance              | $R_G$        |   | $f = 1\text{ MHz}$ |      | 0.45 |    |

### SWITCHING CHARACTERISTICS

|                     |              |  |  |      |  |    |
|---------------------|--------------|--|--|------|--|----|
| Turn-On Delay Time  | $t_{d(ON)}$  | $V_{GS} = 0/10\text{ V}, V_{DD} = 32\text{ V}, I_D = 50\text{ A}, R_G = 0\ \Omega$ |  | 7.33 |  | ns |
| Rise Time           | $t_r$        |  |  | 5.39 |  |    |
| Turn-Off Delay Time | $t_{d(OFF)}$ |  |  | 11.1 |  |    |
| Fall Time           | $t_f$        |  |  | 4.48 |  |    |

### SOURCE TO DRAIN DIODE CHARACTERISTICS

|                         |          |   |                           |  |      |     |    |
|-------------------------|----------|---|---------------------------|--|------|-----|----|
| Forward Diode Voltage   | $V_{SD}$ | $V_{GS} = 0\text{ V}, I_S = 50\text{ A}$                                    | $T_J = 25^\circ\text{C}$  |  | 0.81 | 1.2 | V  |
|                         |          |   | $T_J = 125^\circ\text{C}$ |  | 0.66 |     |    |
| Reverse Recovery Time   | $t_{RR}$ | $V_{DD} = 32\text{ V}, I_F = 50\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$ |                           |  | 94.4 |     | ns |
| Charge Time             | $t_a$    |   |                           |  | 55.6 |     |    |
| Discharge Time          | $t_b$    |   |                           |  | 38.8 |     |    |
| Reverse Recovery Charge | $Q_{RR}$ |   |                           |  | 269  |     |    |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

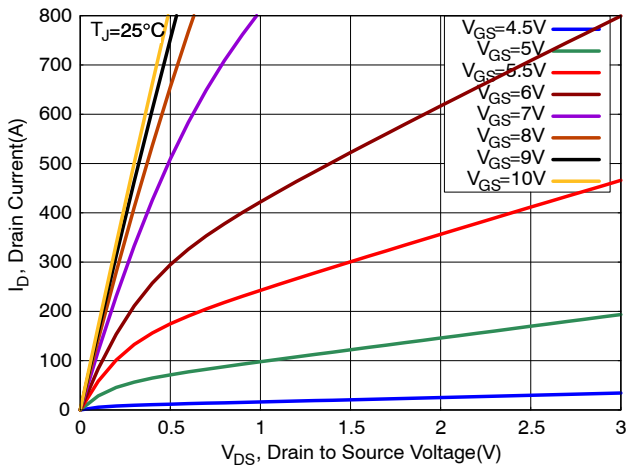


Figure 1. On-Region Characteristics

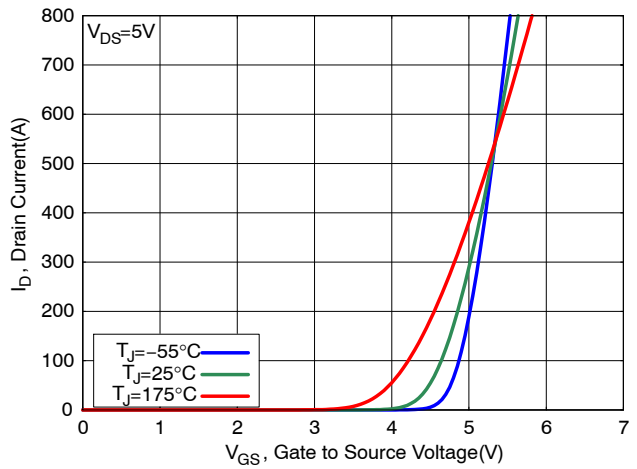


Figure 2. Transfer Characteristics

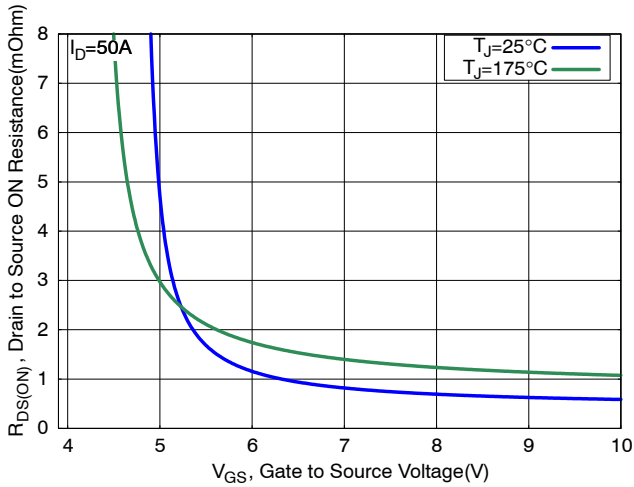


Figure 3. On-Resistance vs. Gate Voltage

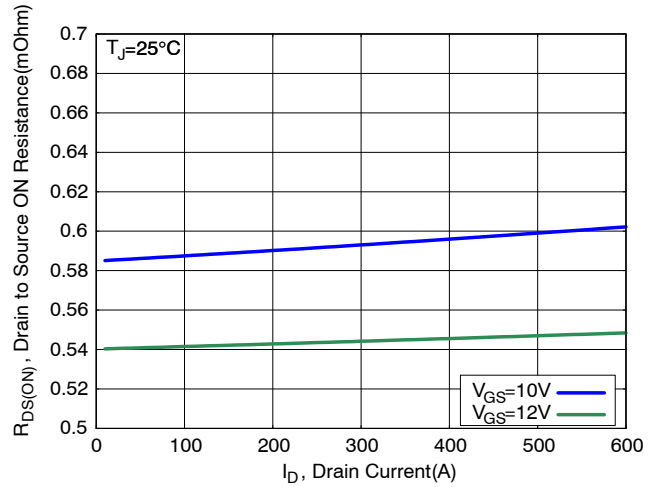


Figure 4. On-Resistance vs. Drain Current

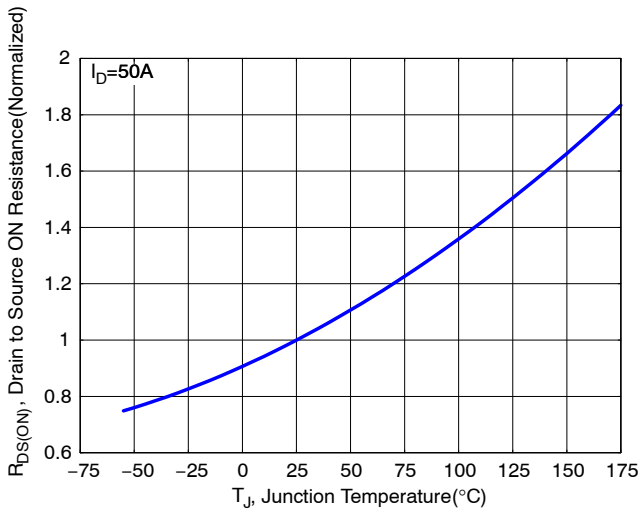


Figure 5. Normalized ON Resistance vs. Junction Temperature

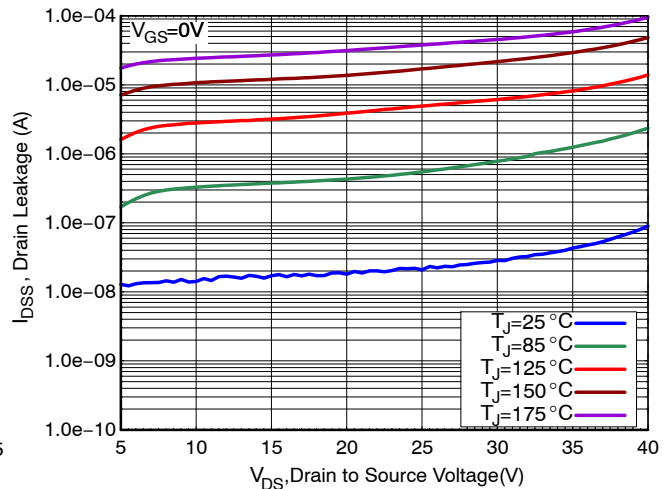


Figure 6. Drain Leakage vs. Drain-to-Source Voltage

# NVMFWS0D7N04XM

## TYPICAL CHARACTERISTICS

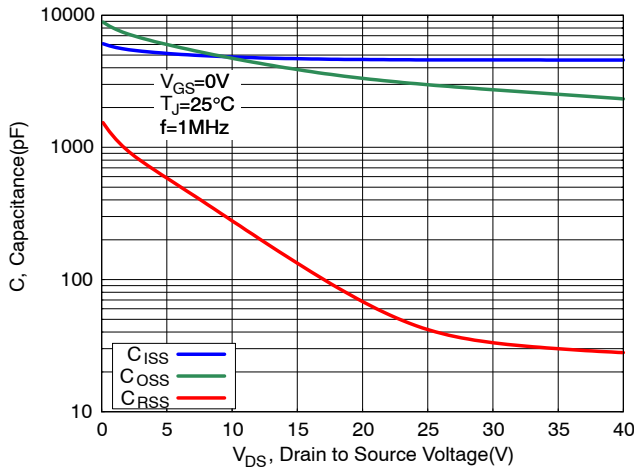


Figure 7. Capacitance Characteristics

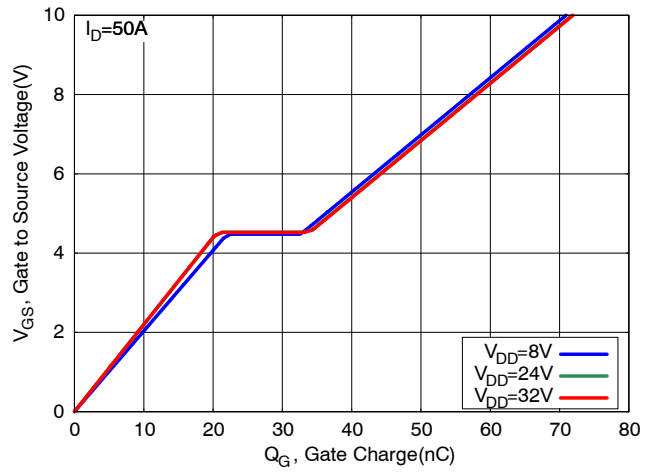


Figure 8. Gate Charge Characteristics

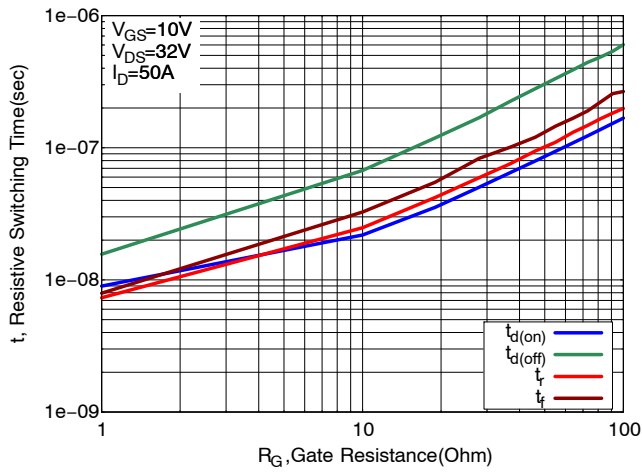


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

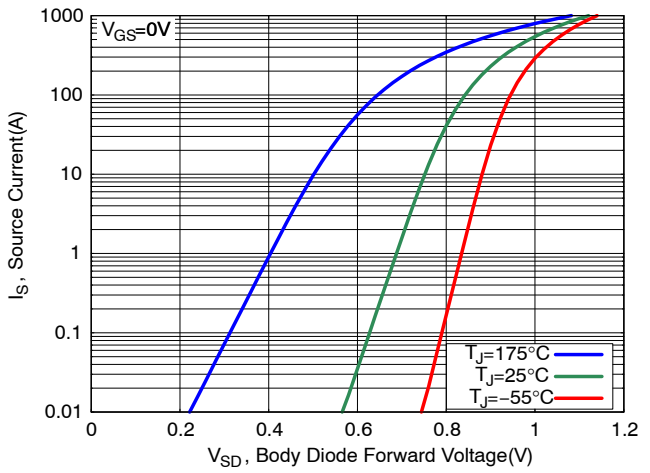


Figure 10. Diode Forward Characteristics

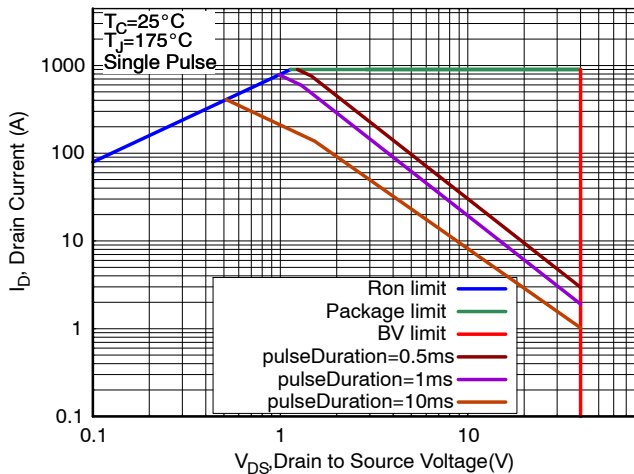


Figure 11. Maximum Rated Forward Biased Safe Operating Area

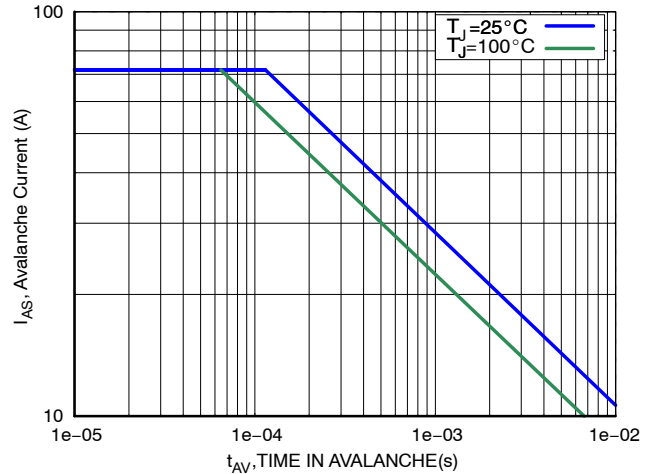


Figure 12.  $I_{peak}$  vs. Time in Avalanche

# NVMFWS0D7N04XM

## TYPICAL CHARACTERISTICS

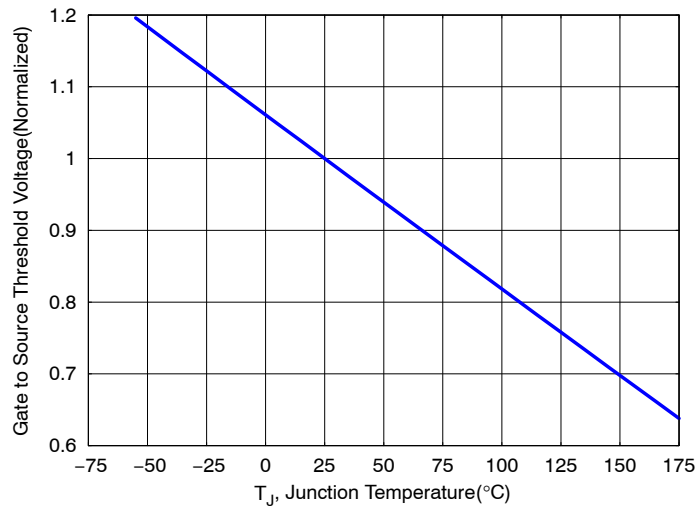


Figure 13. Gate Threshold Voltage vs. Junction Temperature

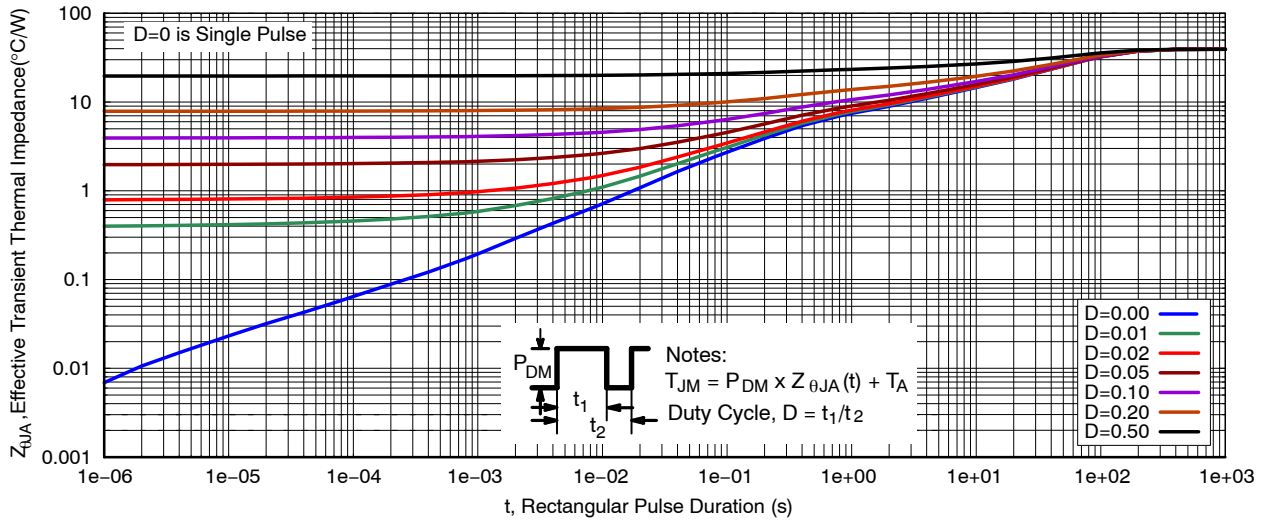


Figure 14. Thermal Response

### ORDERING INFORMATION

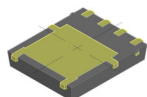
| Device            | Marking | Package            | Shipping <sup>†</sup> |
|-------------------|---------|--------------------|-----------------------|
| NVMFWS0D7N04XMT1G | 0D7N4W  | DFNW5<br>(Pb-Free) | 1500 / Tape & Reel    |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®

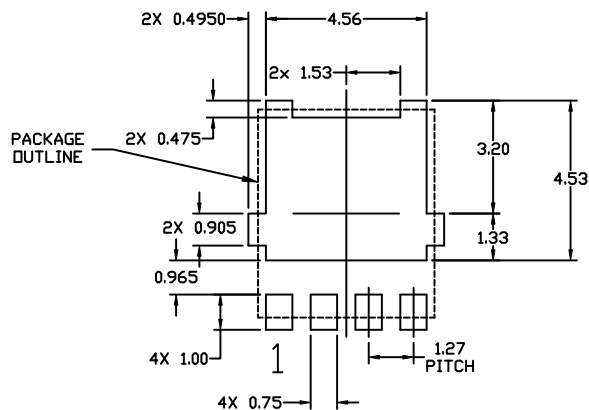
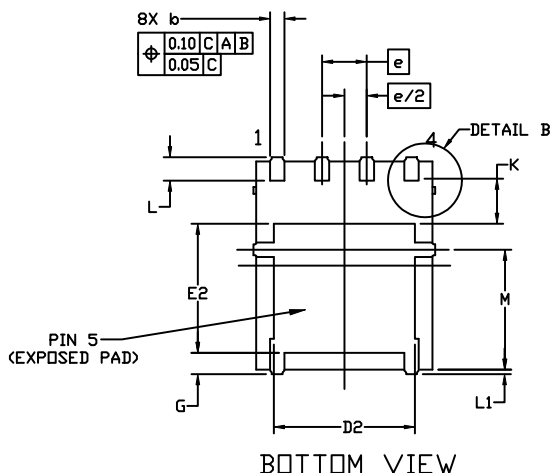
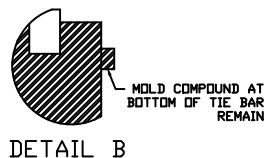
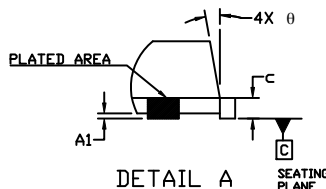
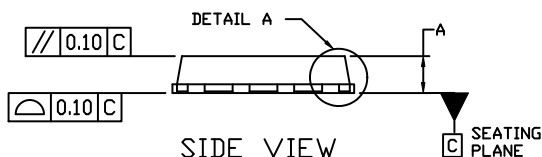
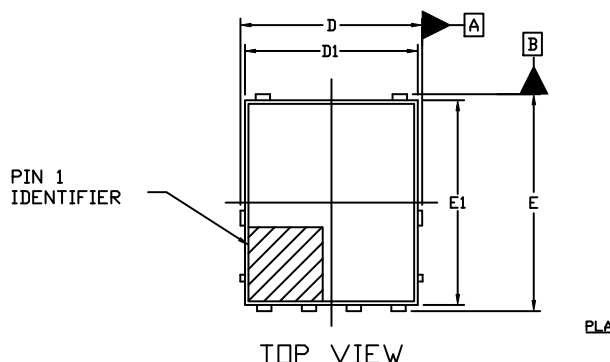


### DFNW5 5x6 (FULL-CUT SO8FL WF)

#### CASE 507BA

#### ISSUE A

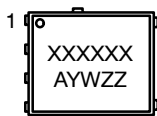
DATE 03 FEB 2021



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
  2. CONTROLLING DIMENSION: MILLIMETERS
  3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
  4. THIS PACKAGE CONTAINS WETTABLE FLANK DESIGN FEATURES TO AID IN FILLET FORMATION ON THE LEADS DURING MOUNTING.

| DIM | MILLIMETERS |       |      |
|-----|-------------|-------|------|
|     | MIN.        | NOM.  | MAX. |
| A   | 0.90        | 1.00  | 1.10 |
| A1  | 0.00        | ---   | 0.05 |
| b   | 0.33        | 0.41  | 0.51 |
| c   | 0.23        | 0.28  | 0.33 |
| D   | 5.00        | 5.15  | 5.30 |
| D1  | 4.70        | 4.90  | 5.10 |
| E   | 6.00        | 6.15  | 6.30 |
| E1  | 5.70        | 5.90  | 6.10 |
| E2  | 3.45        | 3.65  | 3.85 |
| e   | 1.27 BSC    |       |      |
| G   | 0.51        | 0.575 | 0.71 |
| K   | 1.20        | 1.35  | 1.50 |
| L   | 0.51        | 0.575 | 0.71 |
| L1  | 0.150 REF   |       |      |
| M   | 3.00        | 3.40  | 3.80 |
| θ   | 0°          | ---   | 12°  |

### GENERIC MARKING DIAGRAM\*



- XXXXXX = Specific Device Code  
 A = Assembly Location  
 Y = Year  
 W = Work Week  
 ZZ = Lot Traceability
- \*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

- ### RECOMMENDED MOUNTING FOOTPRINT
- \* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

|                         |                                      |  |
|-------------------------|--------------------------------------|--|
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| <b>DESCRIPTION:</b>     | <b>DFNW5 5x6 (FULL-CUT SO8FL WF)</b> | <b>PAGE 1 OF 1</b>   |

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